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(54) Title: SINGLE-ELECTRON TRANSISTORS AND FABRICATION METHODS IN WHICH THE THICKNESS OF AN INSULATING LAYER DEFINES SPACING BETWEEN ELECTRODES

(57) Abstract: Single-electron transistors include first and second electrodes and an insulating layer between them on a substrate. The insulating layer has a thickness that defines a spacing between the first and second electrodes. At least one nanoparticle is provided on the insulating layer. Accordingly, a desired spacing between the first and second electrodes may be obtained without the need for high resolution photolithography. An electrically-gated single-electron transistor may be formed, wherein a gate electrode is provided on the at least nanoparticle opposite the insulating layer end. Alternatively, a chemically-gated single-electron transistor may be formed by providing an analyte-specific binding agent on a surface of the at least one nanoparticle. Arrays of single-electron transistors also may be formed on the substrate. The single-electron transistors may be fabricated by forming a post electrode on a substrate, conformally forming an insulating layer on at least a portion of the post electrode and conformally forming a second electrode on at least a portion of the insulating layer opposite the post electrode. At least one nanoparticle is placed on the insulating layer, between the post electrode and the second electrode.



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**SINGLE-ELECTRON TRANSISTORS AND FABRICATION METHODS IN
WHICH THE THICKNESS OF AN INSULATING LAYER DEFINES
SPACING BETWEEN ELECTRODES**

Field of the Invention

This invention relates to microelectronic devices and fabrication methods therefor, and more particularly to single-electron transistors and fabrication methods therefor.

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Background of the Invention

Single-electron Transistor (SET) devices and fabrication methods are being widely investigated for high density and/or high performance microelectronic devices. As is well known to those having skill in the art, single-electron transistors use single-electron nanoelectronics that can operate based on the flow of single-electrons through nanometer-sized particles, also referred to as nanoparticles, nanoclusters or quantum dots. Although a single-electron transistor can be similar in general principle to a conventional Field Effect Transistor (FET), such as a conventional Metal Oxide Semiconductor FET (MOSFET), in a single-electron transistor, transfer of electrons may take place based on the tunneling of single-electrons through the nanoparticles. Single-electron transistors are described, for example, in U.S. Patent Nos. 5,420,746; 5,646,420; 5,844,834; 6,057,556 and 6,159,620, and in publications by the present inventor Brousseau, III et al., entitled *pH-Gated Single-Electron Tunneling in Chemically Modified Gold Nanoclusters*, Journal of the American Chemical Society, Vol. 120, No. 30, 1998, pp. 7645-7646, and by Feldheim et al., entitled *Self-Assembly of Single Electron Transistors and Related Devices*, Chemical Society Reviews, Vol. 27, 1998, pp. 1-12, and in a publication by Klein et al., entitled *A Single-Electron Transistor Made From a Cadmium Selenide Nanocrystal*, Nature, 1997, pp. 699-701, the disclosures of which are hereby incorporated herein by reference in their entirety as if set forth fully herein.

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A major breakthrough in single-electron transistor technology is described in U.S. Patent Application Serial No. 09/376,695, entitled *Sensing Devices Using Chemically-Gated Single Electron Transistors*, by Daniel L. Feldheim and the present inventor Louis C. Brousseau, III, also published as International Publication No. WO 01/13432 A1, the disclosures of which are hereby incorporated herein by reference in their entirety as if set fully herein. Described therein is a chemically-gated single-electron transistor that can be adapted for use as a chemical or biological sensor. Embodiments of these chemically-gated single-electron transistors include source and drain electrodes on a substrate and a nanoparticle between the source and drain electrodes, that has a spatial dimension of a magnitude of approximately 12nm or less. An analyte-specific binding agent is disposed on a surface of the nanoparticle. A binding event occurring between a target analyte and the binding agent causes a detectable change in the characteristics of the single-electron transistor.

Notwithstanding these and other configurations of single-electron transistors, including chemically-gated single-electron transistors, it may be difficult to fabricate these devices using conventional photolithography that is employed to fabricate microelectronic devices. In particular, in order to provide quantum mechanical effects with nanoparticles, it may be desirable to provide spacing between the source and drain electrodes of a single-electron transistor that is less than about 20nm, or less than about 12nm or about 10nm. It may be difficult, however, to provide these spacings using conventional lithography at low cost and/or with acceptable device yields.

Summary of the Invention

Embodiments of the present invention provide single-electron transistors and manufacturing methods therefor, in which first and second electrodes and an insulating layer therebetween are provided on a substrate. The insulating layer has a thickness that defines a spacing between the first and second electrodes. At least one nanoparticle is provided on the insulating layer. Accordingly, a desired spacing between the first and second electrodes may be obtained without the need for high resolution photolithography.

Embodiments of the present invention may stem from a realization that thin film insulating layers, such as insulating layers that are about 10nm thick, can be fabricated using conventional microelectronic fabrication techniques, such as

chemical vapor deposition, whereas it may be difficult to photolithographically define a region in a layer that is, for example, 10nm wide. According to embodiments of the invention, single-electron structures and fabrication methods may be provided that allow the thickness of an insulating layer between first and second electrodes to
5 determine spacing between the first and second electrodes. Accordingly, single-electron transistor devices may be fabricated using conventional microelectronic techniques with the potential of low cost and/or high yields.

Single-electron transistors according to embodiments of the present invention comprise a substrate including a face. A first electrode extends from the face, and
10 includes a first electrode end and a sidewall. In some embodiments, the first electrode end is remote from the face, and the sidewall extends between the face and the first electrode. The first electrode may be regarded as a post, tower, mesa, tip, pyramid or cone electrode. An insulating layer is provided on the sidewall, the insulating layer including an insulating layer end that is remote from the face. A second electrode is
15 provided on the insulating layer opposite the sidewall. The second electrode includes a second electrode end. At least one nanoparticle is provided on the insulating layer end. In some embodiments, the insulating layer is less than about 20nm thick. In other embodiments, the insulating layer is less than about 12nm thick, and in other embodiments the insulating layer is about 10nm thick.

20 In some embodiments of the present invention, the insulating layer end is a continuous insulating layer end that surrounds the sidewall. In other embodiments, the second electrode end is a continuous second electrode end that surrounds the continuous insulating layer end. In yet other embodiments, the continuous insulating layer end and the continuous second electrode end form first and second rings,
25 respectively, that surround the first electrode end. In still other embodiments, the first and second rings are circular, elliptical and/or polygonal first and second rings. In yet other embodiments, the first electrode insulating end and the second electrode insulating end are coplanar.

In some embodiments, the at least one nanoparticle on the insulating layer end
30 comprises a plurality of nanoparticles on the insulating layer end, wherein the first electrode end and the second electrode end are free of nanoparticles thereon. In other embodiments, nanoparticles also are included on the first electrode end and/or on the second electrode end.

In yet other embodiments, a self-assembled monolayer is provided on the insulating layer end, wherein the at least one nanoparticle is on the self-assembled monolayer, opposite the insulating layer end. In still other embodiments, the self-assembled monolayer also is provided on the first electrode end and/or on the second electrode end.

Embodiments of the invention as described above may be used to form an electrically-gated single-electron transistor, wherein a gate electrode is provided on the at least one nanoparticle opposite the insulating layer end. In other embodiments, a chemically-gated single-electron transistor may be provided by providing an analyte-specific binding agent on a surface of the at least one nanoparticle. Moreover, in any of the above embodiments, arrays of single-electron transistors may be formed on the substrate, wherein an array of first electrodes may be provided on the substrate, portions of a single insulating layer may provide the insulating layers on the array of first electrodes and portions of a single conductive layer may provide an array of second electrodes on the array of first electrodes.

Single-electron transistors may be fabricated, according to embodiments of the present invention, by forming a first electrode on a substrate, conformally forming an insulating layer on at least a portion of the first electrode and conformally forming a second electrode on at least a portion of the insulating layer opposite the first electrode. At least one nanoparticle is placed on the insulating layer, between the first electrode and the second electrode.

In some method embodiments, the first electrode is formed by forming a mask region on the substrate and anisotropically etching the substrate with the mask region thereon, to form the first electrode on the first substrate having a first electrode end, with the mask region on the first electrode end. In some embodiments, the insulator is conformally formed on the first electrode, except for the first electrode end that has the mask region thereon and the second electrode is conformally formed on the insulating layer, except for the first electrode end that has the mask region thereon. Moreover, in other embodiments, the mask region is removed from the first electrode end prior to placing the nanoparticle. The nanoparticle is placed on the insulating layer adjacent the first electrode end.

In other method embodiments, the second electrode and the insulating layer are removed from the first electrode end prior to placing the at least one nanoparticle on the insulating layer. The second electrode and the insulating layer may be

removed from the first electrode end by forming a recessed layer on the substrate, such that the first electrode end, the insulating layer on the first electrode end and the second electrode on the first electrode end protrude from the recessed layer. The first electrode, the insulating layer on the first electrode end and the second electrode layer on the first electrode end that protrude from the recessed layer are then planarized. Accordingly, the thickness of the insulating layer may determine the spacing between the first and second electrodes, to thereby allow a single-electron transistor to be fabricated using conventional microelectronic processing steps, while allowing high performance and/or high yields.

Brief Description of the Drawings

Figures 1A, 2A and 3-9 are side cross-sectional views of single-electron transistors according to embodiments of the present invention.

Figures 1B-1D and 2B-2D are top views of single-electron transistors according to embodiments of the present invention.

Figures 10A-10F and 11A-11I are side cross-sectional views of single-electron transistors according to embodiments of the present invention, during intermediate fabrication steps according to embodiments of the present invention.

Detailed Description of Preferred Embodiments

The present invention now will be described more fully hereinafter with reference to the accompanying drawings, in which embodiments of the invention are shown. This invention may, however, be embodied in many different forms and should not be construed as limited to the embodiments set forth herein. Rather, these embodiments are provided so that this disclosure will be thorough and complete, and will fully convey the scope of the invention to those skilled in the art. In the drawings, the thickness of layers and regions may be exaggerated for clarity. Like numbers refer to like elements throughout.

Figures 1A and 1B are a side cross-sectional view and a top view, respectively, of single-electron transistors according to embodiments of the present invention. As shown in Figures 1A and 1B, these embodiments of single-electron transistors include a substrate 100 including a face 100a. As is well known to those having skill in the art, the substrate can comprise a conventional monocrystalline silicon substrate, a semiconductor-on-insulator (SOI) substrate, a silicon carbide,

gallium arsenide, gallium nitride, diamond thin film and/or other substrate, and may also include one or more heteroepitaxial and/or homoepitaxial layers on the substrate. The substrate face 100a may be planar, or non-planar (three-dimensional).

Still referring to Figures 1A and 1B, a first electrode 150 is provided that
5 extends from the face. The first electrode 150 includes a first electrode end 150a that is illustrated in Figure 1A as being remote from the face 100a and a sidewall 150b. In Figure 1A, the sidewall 150b extends between the face 100a and the first electrode end 150a. Embodiments of the first electrode 150 may be regarded as a post, tower, mesa, tip, pyramid or cone electrode. It will be understood that the first electrode 150
10 may be conductive or may include a portion thereof that is conductive at least adjacent the end 150a thereof. The first electrode 150 may comprise any of the materials that were described above for the substrate 100, and may also include other conductive materials, such as conductive polysilicon, metal and/or other conductive materials. Although the first electrode 150 is illustrated in Figure 1A as extending
15 orthogonal to the substrate 100, it also may be oblique or parallel thereto. Moreover, although the sidewall 150b is illustrated as forming an obtuse angle with the face 100a, it may also form a right angle or an acute angle. The sidewall 150b also need not be linear.

Still referring to Figures 1A and 1B, an insulating layer 110 is provided on the
20 sidewall 150b. The insulating layer 110 includes an insulating layer end 110a that is remote from the face 100. The insulating layer 110 preferably is a layer of silicon dioxide, silicon nitride, high dielectric constant material and/or other dielectric materials, or multiple sublayers thereof, that can be formed using conventional microelectronic processes, such as Plasma-Enhanced Chemical Vapor Deposition
25 (PECVD), so that the insulating layer 110 may be made relatively thin with high controllability and reliability. More specifically, the thickness 110b of the insulating layer 110 may be less than about 20nm thick, or less than about 12nm thick, or about 10nm thick. The formation of conformal insulating layers on microelectronic substrates is well known to those having skill in the art and need not be described
30 further herein. For example, thin insulators are conventionally used to form the gate insulating layer of MOSFETs. In other embodiments, the insulating layer 110 can include one or more self-assembled monolayers and/or polymer films.

Still referring to Figures 1A and 1B, a second electrode 120 is provided on the insulating layer 110 opposite the sidewall 150b. The second electrode 120 includes a

second electrode end 120a. The second electrode 120 can comprise a layer or multiple sublayers comprising metal, doped polysilicon and/or other conventional conductive materials, and may be deposited conformally using conventional deposition or other techniques. The deposition of conformal metal layers on microelectronic substrates is well known to those having skill in the art and need not be described further herein. For example, conformal metal layers are conventionally used for electrodes and wiring layers of MOSFETs.

Finally, referring to Figures 1A and 1B, at least one nanoparticle 140 is provided on the insulating layer end 110a. The fabrication of at least one nanoparticle 140 on an insulating layer is described, for example, in the above-incorporated Brousseau et al., Feldheim et al. and Klein et al. publications, and need not be described further herein.

In some embodiments, as shown in Figures 1A and 1B, a self-assembled monolayer 130 is provided between the at least one nanoparticle 140 and the insulating layer end 110a. Chemical interactions can be used to anchor a nanoparticle on a surface, for example, pursuant to the techniques that are described in a publication to Ulman, entitled *Formation and Structure of Self-Assembled Monolayers*, Chemical Review, 1996, pp. 1533-1554. Processes which can be used to attach molecular receptor probes to surfaces using self-assembled nanolayers are described in Lenigk et al., *Surface Characterization of a Silicon-Chip-Based DNA Microarray*, Langmuir, 2001, pp. 2497-2501. The disclosures of both of these publications are hereby incorporated herein by reference in their entirety as if set forth fully herein, and need not be described further herein. Also, some polymers have shown affinity for nanoparticle adhesion, or can be chemically modified to have a strong affinity, which can be used as an anchor layer.

As shown in Figure 1A, the thickness 110b of the insulating layer 110 may be used to control the spacing between the first electrode end 150a and the second electrode end 120a, so as to provide quantum mechanical tunneling therebetween through the at least one nanoparticle 140. Since the thickness 110b of the insulating layer 110 may be well-controlled on a nanometer scale using conventional microelectronic techniques, the desired spacing for a single-electron transistor may be obtained relatively inexpensively and/or with relatively high yields.

In embodiments shown in Figures 1A and 1B, the insulating layer end 110a is a continuous insulating layer end that surrounds the sidewall 150b. However, a

discontinuous insulating layer end may be provided, as well. Moreover, in Figures 1A and 1B, the second electrode end 120a is illustrated as a continuous second electrode end that surrounds the continuous insulating layer end 110a. However, in other embodiments, a discontinuous second electrode end may be provided.

5 Thus, in Figures 1A and 1B, the continuous insulating layer end 110a and the continuous second electrode end 120a form first and second rings, respectively, that surround the first electrode end 150a. Moreover, in Figures 1A and 1B, the first and second rings are circular first and second rings.

Figures 1C and 1D are top views of other embodiments of the present
10 invention, wherein the first and second rings 110a and 120a of Figure 1B are elliptical first and second rings 110a' and 120a', or polygonal first and second rings 110a'' and 120a'', respectively. The first electrode end may be an elliptical or polygonal first electrode end 150a' or 150a'', respectively, as well. Moreover, in Figure 1A, the first electrode end 150a, the insulating layer end 110a and the second electrode end 120a
15 are coplanar. However, they need not be coplanar and they need not extend parallel to the substrate face 100.

From a dimensional standpoint, the first electrode end 150a, 150a', 150a'' may have a diameter or longest dimension that is on the order of 100nm. The insulating layer 110 may have thickness 110b that is between about 10nm and about
20 20nm, and the second electrode 120a, 120a', 120a'' may have a thickness of between about 10nm and about 20 nm. Functionally, the thickness 110b of the insulating layer 110 may be used to support quantum mechanical tunneling using the nanoparticles 140, whereas the size of the first and second electrodes 150 and 120 may vary over a wide range, based on many other considerations, such as a desired overall size for the
25 single-electron transistor, structural soundness, etc.

The self-assembled monolayer 130 may maintain at least one nanoparticle 140 at a distance of about 1nm from both the first electrode end 150a and from the second electrode end 120a. However, distances of between about 0.5nm to about 5nm also may be used in other embodiments. Other distances also may be used.

30 In embodiments of Figures 1A-1D, a plurality of nanoparticles 140 are provided on the insulating layer end 110a, whereas the first electrode ends 150a, 150a', 150a'', and the second electrode ends 120a, 120a', 120a'' are free of nanoparticles 140 thereon. However, in other embodiments of the invention, as shown in Figures 2A-2D, a plurality of nanoparticles 240 are provided on the

insulating layer end 110a, 110a', 110a" on the first electrode end 150a, 150a', 150a", and on the second electrode end 120a, 120a', 120a". It also will be understood that the nanoparticles 240 may be provided on either the first electrode end 150a, 150a', 150a" or the second electrode end 120a, 120a', 120a". Moreover, the plurality of nanoparticles 240 may be randomly spaced and/or may be spaced in a linear and/or nonlinear, orthogonal and/or non-orthogonal array of equally and/or unequally (aperiodic and/or random) spaced apart nanoparticles. The nanoparticles 240 may have a predetermined relationship to the underlying layers and/or a random relationship thereto.

10 Figures 3 and 4 are cross-sectional views of single-electron transistors according to other embodiments of the invention. In these embodiments, an insulating layer or sublayers 330, 430, comprising silicon dioxide, silicon nitride and/or other conventional insulating layers, are provided between the at least one nanoparticle 140, 240, and the first electrode end 150a, the insulating layer end 110a and/or the second electrode end 120a. The use of an insulating layer to anchor a nanoparticle is described, for example in Andres et al., *"Coulomb Staircase" Single Electron Tunneling at Room Temperature in a Self Assembled Molecular Nanostructure*, Science, 1996, Vol. 272, pp. 1323-1325, the disclosure of which is hereby incorporated herein by reference in its entirety as if set forth fully herein, and need not be described further herein. It also will be understood that the insulating layer 330 may comprise a portion of the insulating layer 110. In yet other embodiments, both an insulating layer 330, 430 of Figures 3 and 4, and a self-assembled monolayer 130 of Figures 1 and 2 may be used in combination. Other intermediary layers also may be used.

25 Figure 5 is a cross-sectional view of yet other embodiments of the present invention, wherein an analyte-specific binding agent 560 is provided on a surface of the at least one nanoparticle 140, to provide a chemically-gated single electrode transistor. An analyte-specific binding agent 560 of Figure 5 also may be provided on any of the embodiments that were described in connection with any of the preceding figures, to provide a chemically-gated single-electron transistor. Analyte-specific binding agents are described, for example in the above-incorporated Ulman, Lenigk et al., Feldheim et al. and Brousseau et al. publications, and need not be described further herein.

Figure 6 is a cross-sectional view of other embodiments of the present invention, wherein a gate electrode 670 is provided on the at least one nanoparticle 140 opposite the insulating layer end 110a, to provide a single-electron field effect transistor. Single layer and/or multilayer gate electrodes may be provided. A gate electrode also may be provided in any of the embodiments that are described in connection with any of the figures herein. An insulating layer also may be provided between the gate electrode 670 and the at least one nanoparticle, to provide an insulated gate electrode.

In all of the above-described embodiments, only one single-electron transistor is illustrated on a substrate. However, as illustrated in Figure 7, an array of single-electron transistors 710a-710n may be provided on a substrate. One- and/or two-dimensional, linear and/or nonlinear, orthogonal and/or nonorthogonal arrays may be provided, with the spacing among the single-electron transistors being equal (periodic) and/or unequal (aperiodic and/or random). Each single-electron transistor 710a-710n may be identical, or at least some of the single-electron transistors may be dissimilar. Moreover, any of the embodiments of the figures herein may be used for any of the single-electron transistors 710a-710n. Finally, in these embodiments, the insulating layers 110 of some or all of the array of single-electron transistors 710a-710n may comprise portions of a single insulating layer. Moreover, the second electrodes 120 of some or all of the single-electron transistors 710a-710n may comprise portions of a single conductive layer.

Figure 8 is a cross-sectional view of yet other embodiments of the present invention that include extended insulating layers and/or electrodes. In particular, in Figure 8, the insulating layer 110' and the second electrode 120' both extend along the substrate face 100a, in addition to extending along the first electrode sidewall 150b. It also will be understood that only one of the insulating layer 110' or the second electrode 120' may extend along the substrate face 100a. Any of the configurations that are described in connection with any of the figures herein may be combined with the extended insulating layer 110' and/or extended second electrode 120' of Figure 8.

Still referring to Figure 8, a second insulating layer 810 also may be provided on the second electrode 120' opposite the insulating layer 110'. The second insulating layer 810 may comprise a layer or multiple sublayers comprising silicon dioxide, silicon nitride one or more self-assembled monolayers, one or more polymer films and/or other materials that may be used to protect a device from an outside (ambient)

environment. The second insulating layer 810 may be a specialized layer that may depend upon the ambient in which a chemically-gated single-electron transistor is being used. The second insulating layer 810 may be used with or without the extended layers 110' and 120' of Figure 8, and/or with any other embodiments that are described in connection with any of the figures herein.

Figure 9 is a cross-sectional view of other embodiments of the present invention. In Figure 9, external electrical contacts are provided using a conductive via 910 that electrically connects the second electrode 120' to a pad 920 on the back face of the substrate 100. The first electrode 150 also may contact the back face of the substrate 100 at a second pad 930 using internal doped regions of the substrate and/or other conventional techniques. Appropriate insulating regions may be provided to electrically insulate the first and second pads 920 and 930 from one another and/or to insulate the conductive via 910 from other regions, using techniques well known to those having skill in the art. Solder bumps and/or other interconnect techniques may be used to electrically and/or mechanically connect the first and second contact pads 920 and 930 to an external device. These and other external contact schemes also may be used with any of the described embodiments of the invention.

Figures 10A-10F are cross-sectional views of single-electron transistors according to embodiments of the present invention, during intermediate fabrication steps according to embodiments of the present invention. These method embodiments may be used to fabricate single-electron transistors as illustrated in Figure 1A. However, similar method embodiments may be used to fabricate single-electron transistors of Figures 1B-9 and/or combinations thereof.

Referring now to Figure 10A, a mask region 1010 is formed on a substrate 1000, for example by forming a conventional mask comprising silicon nitride on a conventional substrate, and then patterning using conventional photolithography. It will be understood that since the width of the mask region 1010 need not determine the spacing between the first and second electrodes that are formed subsequently, conventional photolithography may be used. It also will be understood that the substrate 1000 may be a conventional substrate, as was described in connection with Figure 1A, such as a layer of doped polysilicon and/or other conductive material on a monocrystalline silicon substrate.

Then, referring to Figure 10B, an anisotropic (wet) etch may be performed using the masking region 1010 as an etching mask, to form the first electrode 150 on a substrate 100. Other conventional etching techniques and/or other conventional post-forming techniques such as selective epitaxial growth, may be used.

5 Referring now to Figure 10C, the insulating layer 110 is formed, for example by performing a conformal deposition, for example using Chemical Vapor Deposition (CVD), such as Plasma-Enhanced Chemical Vapor Deposition (PECVD), which may not form a continuous insulating layer on the mask region. It also will be understood that the insulating layer 110 also may be formed on the mask region 1010.

10 Then, referring to Figure 10D, the second electrode 120 is formed on the insulating layer 110, for example using a directional (angled) deposition technique, which may not form a continuous layer on the mask region 1010. Alternatively, other deposition techniques may be performed which may also form a conformal layer on the mask region 1010.

15 Then, referring to Figure 10E, the mask region 1010 is removed, which may also remove any portions of the insulating layer 110 and/or the second electrode 120 thereon, to thereby define the first electrode end 150a, the insulating layer end 110a, and the second electrode end 120a.

Referring now to Figure 10F, absorption of the anchoring self-assembled
20 monolayer 130 may be performed, for example, using techniques that were described above. At least one nanoparticle 140 then is attached to the anchoring self-assembled monolayer 130, for example, using techniques that were described above.

Figures 11A-11I are cross-sectional views of other single-electron transistors according to embodiments of the present invention, during intermediate fabrication
25 steps according to embodiments of the present invention. As shown in Figure 11A, a mask region 1010 is formed on a substrate, similar to Figure 10A. As shown in Figure 11B, anisotropic etching and/or other techniques are used to create a first (post) electrode 150, similar to Figure 10B. As shown in Figure 11C, the masking region 1010 then is removed. In Figure 11D, a conformal insulating layer 1110 is
30 formed on the first electrode 150, for example, using conventional conformal deposition techniques. In other embodiments, directional deposition may need not be used. As shown in Figure 11E, a conformal second conductive layer 1120 is formed on the conformal insulating layer 1110, for example using conventional conformal deposition techniques. In other embodiments, directional deposition may not need to

be used. Layers 1110 and 1120 may comprise materials that were described earlier for layers 110 and 120, respectively.

Referring now to Figure 11F, a recessed layer 1130 then may be formed between structures of Figure 11B. The recessed layer 1130 may include one or more sublayers comprising silicon dioxide, silicon nitride, polyimide and/or other materials that are compatible with a subsequent selective etching and/or chemical-mechanical polishing process. The recessed layer 1130 may be recessed from the top of the conductive layer 1120 by at least the thickness of layers 1110 and 1120. However, smaller or larger recesses also may be provided.

Referring now to Figure 11G, chemical-mechanical polishing and/or other conventional techniques are used to planarize the structure, and thereby define the insulating layer 110 including the insulating layer end 110a, and the second electrode 120 including the second electrode end 120a. Referring now to Figure 11H, the recessed layer 1130 is removed using conventional techniques, to provide a structure similar to Figure 10E. Finally, at Figure 11I, at least one nanoparticle 140 and an optional self-aligned monolayer 130 are formed as was described in connection with Figure 10F.

Accordingly, embodiments of the present invention can provide arrays, including large arrays, of dual concentric electrodes. A conducting center electrode and an outer ring electrode can allow electrochemical reactions to be monitored at the apexes of each electrode-insulator-electrode tower. The electrodes may be derivatized to include chemical specificity to reactions taking place at the surfaces. Enhanced sensitivity can be made possible by attaching nanometer-sized colloidal particles to the insulating regions between the electrodes, which can create single-electron transistors. The colloids can be functionalized with chemically-specific receptors and/or molecules, to incorporate specificity to these reactions.

Single-electron transistors or arrays thereof, according to embodiments of the invention, may be used, for example, as sensing platforms in the wells of microtiter plates, for biological assays. Their enhanced sensitivity compared to conventional larger electrodes can benefit drug discovery and/or biochemistry. Their small size also can afford direct insertion of the arrays into living cells, which can allow *in vivo* chemical study and/or direct mapping of chemical pathways and/or concentrations within the cells.

In the drawings and specification, there have been disclosed typical preferred embodiments of the invention and, although specific terms are employed, they are used in a generic and descriptive sense only and not for purposes of limitation, the scope of the invention being set forth in the following claims.

What is Claimed is:

1. A single-electron transistor comprising:
a substrate including a face;
a first electrode that extends from the face, the first electrode including a first electrode end and a sidewall;
5 an insulating layer on the sidewall, the insulating layer including an insulating layer end that is remote from the face;
a second electrode on the insulating layer opposite the sidewall, the second electrode including a second electrode end that is remote from the face; and
at least one nanoparticle on the insulating layer end.
- 10 2. A single-electron transistor according to Claim 1 wherein the insulating layer is less than about 20nm thick.
3. A single-electron transistor according to Claim 1 wherein the
15 insulating layer is about 10nm thick.
4. A single-electron transistor according to Claim 1 wherein the insulating layer end is a continuous insulating layer end that surrounds the sidewall.
- 20 5. A single-electron transistor according to Claim 4 wherein the second electrode end is a continuous second electrode end that surrounds the continuous insulating layer end.
6. A single-electron transistor according to Claim 5 wherein the
25 continuous insulating layer end and the continuous second electrode end form first and second rings, respectively, that surround the first electrode end.
7. A single-electron transistor according to Claim 6 wherein the first and second rings are circular, elliptical or polygonal first and second rings.
- 30 8. A single-electron transistor according to Claim 1 wherein the first electrode end, the insulating layer end and the second electrode end are coplanar.

9. A single-electron transistor according to Claim 1 wherein the at least one nanoparticle on the insulating layer end comprises a plurality of nanoparticles on the insulating layer end, wherein the first electrode end and the second electrode end are free of nanoparticles thereon.

5

10. A single-electron transistor according to Claim 1 wherein the at least one nanoparticle on the insulating layer end comprises a plurality of nanoparticles on the insulating layer end, on the first electrode end and on the second electrode end.

10

11. A single-electron transistor according to Claim 6 wherein the at least one nanoparticle on the insulating layer end comprises a plurality of nanoparticles on the first ring, wherein the first electrode end and the second ring are free of nanoparticles thereon.

15

12. A single-electron transistor according to Claim 6 wherein the at least one nanoparticle on the insulating layer end comprises a plurality of nanoparticles on the first ring, on the first electrode end and on the second ring.

20

13. A single-electron transistor according to Claim 1 further comprising:
a self-assembled monolayer on the insulating layer end, wherein the at least one nanoparticle is on the self-assembled monolayer, opposite the insulating layer end.

25

14. A single-electron transistor according to Claim 1 further comprising:
a self-assembled monolayer on the insulating layer end, on the first electrode end and on the second electrode end, wherein the at least one nanoparticle comprises a plurality of nanoparticles on the self-assembled monolayer, opposite the insulating layer end, the first electrode end and the second electrode end.

30

15. A single-electron transistor according to Claim 14 further comprising:
a second insulating layer between the self-assembled monolayer and the insulating layer end, the first electrode end and the second electrode end.

16. A single-electron transistor according to Claim 1 further comprising:

an analyte-specific binding agent on a surface of the at least one nanoparticle to provide a chemically-gated single-electron transistor.

17. A single-electron transistor according to Claim 1 in combination with:
5 a gate electrode on the at least one nanoparticle opposite the insulating layer end to provide a single-electron field effect transistor.

18. A single-electron transistor according to Claim 1 in combination with:
a third electrode that extends from the face, spaced apart from the first
10 electrode, the third electrode including a third electrode end that is remote from the face and a third electrode sidewall between the face and the third electrode end;
a second insulating layer on the third electrode sidewall, the second insulating layer including a second insulating layer end that is remote from the face;
a fourth electrode on the second insulating layer opposite the third electrode
15 sidewall, the fourth electrode including a fourth electrode end; and
at least one nanoparticle on the second insulating layer end.

19. A single-electron transistor according to Claim 18 wherein the insulating layer and the second insulating layer comprise first and second portions,
20 respectively, of a single insulating layer, and wherein the second electrode and the fourth electrode comprises first and second portions, respectively, of a single conductive layer.

20. A single-electron transistor according to Claim 1 further comprising a
25 second insulating layer on the second electrode, opposite the insulating layer.

21. A single-electron transistor according to Claim 1 wherein the first electrode end is remote from the face and wherein the sidewall extends between the face and the first electrode end.

30

22. A single-electron transistor comprising:
first and second electrodes and an insulating layer therebetween on a substrate, the insulating layer having a thickness that defines a spacing between the first and second electrodes; and

at least one nanoparticle on the insulating layer.

23. A single-electron transistor according to Claim 22 wherein the insulating layer is less than about 20nm thick.

5

24. A single-electron transistor according to Claim 22 wherein the insulating layer is about 10nm thick.

25. A single-electron transistor according to Claim 22 wherein the at least one nanoparticle on the insulating layer comprises a plurality of nanoparticles on the insulating layer, wherein the first electrode and the second electrode are free of nanoparticles thereon.

26. A single-electron transistor according to Claim 22 wherein the at least one nanoparticle on the insulating layer comprises a plurality of nanoparticles on the insulating layer, on the first electrode and on the second electrode.

27. A single-electron transistor according to Claim 22 further comprising: a self-assembled monolayer on the insulating layer, wherein the at least one nanoparticle is on the self-assembled monolayer, opposite the insulating layer.

28. A single-electron transistor according to Claim 22 further comprising: a self-assembled monolayer on the insulating layer, on the first electrode and on the second electrode, wherein the at least one nanoparticle comprises a plurality of nanoparticles on the self-assembled monolayer, opposite the insulating layer, the first electrode and the second electrode.

29. A single-electron transistor according to Claim 28 further comprising: a second insulating layer between the self-assembled monolayer and the insulating layer, the first electrode and the second electrode.

30. A single-electron transistor according to Claim 22 further comprising: an analyte-specific binding agent on a surface of the at least one nanoparticle to provide a chemically-gated single-electron transistor.

31. A single-electron transistor according to Claim 22 further comprising:
a gate electrode on the at least one nanoparticle opposite the insulating layer to
provide a single-electron field effect transistor.

5

32. A method of fabricating a single-electron transistor comprising:
forming a first electrode on a substrate;
conformally forming an insulating layer on at least a portion of the first
electrode;

10 conformally forming a second electrode on at least a portion of the insulating
layer opposite the first electrode; and
placing at least one nanoparticle on the insulating layer, between the first
electrode and the second electrode.

15 33. A method according to Claim 32 wherein the forming a first electrode
comprises:

forming a mask region on the substrate; and
anisotropically etching the substrate with the mask region thereon, to form the
first electrode on the substrate having a first electrode end, with the mask region on
20 the first electrode end.

34. A method according to Claim 33:
wherein the conformally forming an insulating layer comprises conformally
forming an insulator on the first electrode except for on the first electrode end that has
25 the mask region thereon; and

wherein the conformally forming a second electrode comprises conformally
forming a second electrode on the insulating layer but not on the first electrode end
that has the mask region thereon.

30 35. A method according to Claim 34 wherein the following is performed
between the conformally forming a second electrode and the placing a nanoparticle:
removing the mask region from the first electrode end.

36. A method according to Claim 35 wherein the placing a nanoparticle comprises placing a nanoparticle on the insulating layer, adjacent the first electrode end.

5 37. A method according to Claim 32 wherein the first electrode includes a first electrode end and wherein the following is performed between the conformally forming a second electrode and the placing at least one nanoparticle:

removing the second electrode and the insulating layer from the first electrode end.

10

38. A method according to Claim 37 wherein the placing a nanoparticle comprises placing a nanoparticle on the insulating layer, adjacent the first electrode end.

15 39. A method according to Claim 37 wherein the removing comprises:
forming a recessed layer on the substrate such that the first electrode end, the insulating layer on the first electrode end and the second electrode on the first electrode end protrude from the recessed layer; and

planarizing the first electrode end, the insulating layer on the first electrode
20 end and the second electrode on the first electrode end that protrude from the recessed layer.

40. A method according to Claim 32 wherein the insulating layer is less
than about 20nm thick.

25

41. A method according to Claim 40 wherein the insulating layer is about 10nm thick.

42. A method according to Claim 32 wherein the placing comprises
30 placing a plurality of nanoparticles on the insulating layer, between the first electrode and the second electrode, wherein the first electrode and the second electrode are free of nanoparticles thereon.

43. A method according to Claim 32 wherein the placing comprises placing a plurality of nanoparticles on the insulating layer, between the first electrode and the second electrode, on the first electrode and on the second electrode.

5 44. A method according to Claim 32:
wherein the following is performed between the conformally forming a second electrode and the placing at least one nanoparticle:

forming a self-assembled monolayer on the insulating layer, between the first electrode and the second electrode; and

10 wherein the placing at least one nanoparticle comprises placing at least one nanoparticle on the self-assembled monolayer, opposite the insulating layer.

45. A method according to Claim 44:

15 wherein the following is performed between the conformally forming a second electrode and the forming a self-assembled monolayer:

forming a second insulating layer on the insulating layer; and

wherein the forming a self-assembled monolayer comprises forming a self-assembled monolayer on the second insulating layer, opposite the insulating layer.

20 46. A method according to Claim 32 further comprising:
forming an analyte-specific binding agent on a surface of the at least one nanoparticle to provide a chemically-gated single-electron transistor.

47. A method according to Claim 32 further comprising:

25 forming a gate electrode on the at least one nanoparticle opposite the insulating layer to provide a single-electron field effect transistor.

48. A method according to Claim 32 further comprising forming a second insulating layer on the second electrode, opposite the insulating layer.

30

49. A method of fabricating a single-electron transistor comprising:

forming first and second electrodes and an insulating layer therebetween on a substrate, such that the thickness of the insulating layer defines a spacing between the first and second electrodes; and

placing at least one nanoparticle on the insulating layer.

50. A method according to Claim 49 wherein the insulating layer is less than about 20nm thick.

5

51. A method according to Claim 50 wherein the insulating layer is about 10nm thick.

52. A method according to Claim 49 wherein the placing comprises
10 placing a plurality of nanoparticles on the insulating layer, between the first electrode and the second electrode, wherein the first electrode and the second electrode are free of nanoparticles thereon.

53. A method according to Claim 49 wherein the placing comprises
15 placing a plurality of nanoparticles on the insulating layer, between the first electrode and the second electrode, on the first electrode and on the second electrode.

54. A method according to Claim 49:
wherein the following is performed between the forming and the placing:
20 forming a self-assembled monolayer on the insulating layer,
between the first electrode and the second electrode; and
wherein the placing comprises placing at least one nanoparticle on the self-assembled monolayer, opposite the insulating layer.

25 55. A method according to Claim 54:
wherein the following is performed between the forming first and second electrodes and an insulating layer therebetween and the forming a self-assembled monolayer:

forming a second insulating layer on the insulating layer; and
30 wherein the forming a self-assembled monolayer comprises forming a self-assembled monolayer on the second insulating layer, opposite the insulating layer.

56. A method according to Claim 49 further comprising:

forming an analyte-specific binding agent on a surface of the at least one nanoparticle to provide a chemically-gated single-electron transistor.

57. A method according to Claim 49 further comprising:
5. forming a gate electrode on the at least one nanoparticle opposite the insulating layer to provide a single-electron field effect transistor.

58. A method according to Claim 49 further comprising forming a second insulating layer on the second electrode, opposite the insulating layer.

FIG. 1A

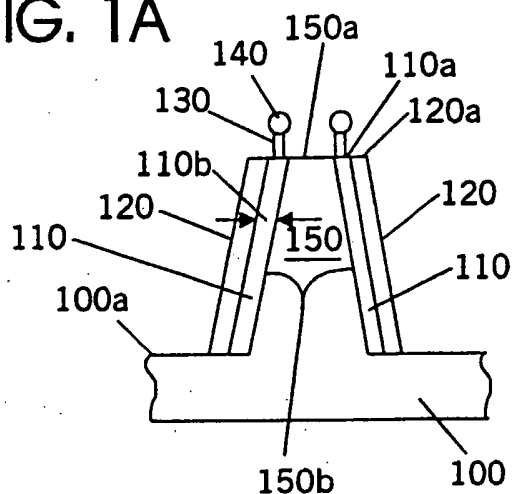


FIG. 1B

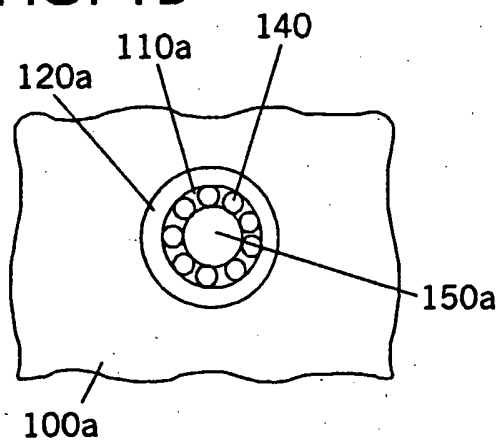


FIG. 1C

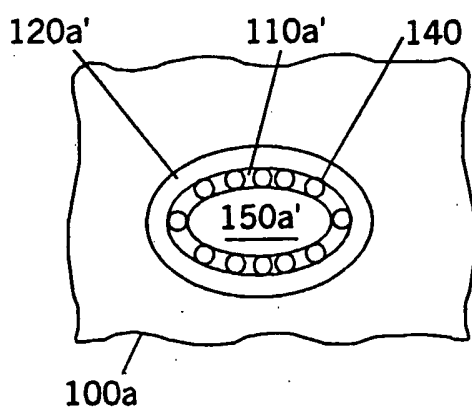


FIG. 1D

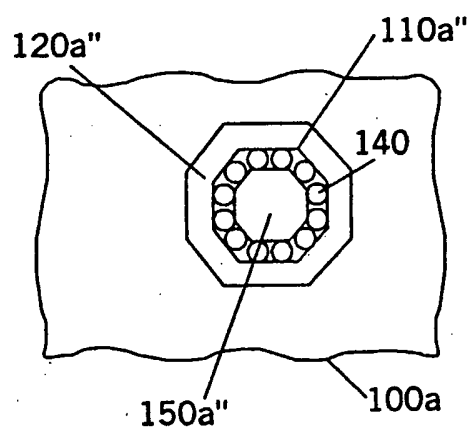


FIG. 2A

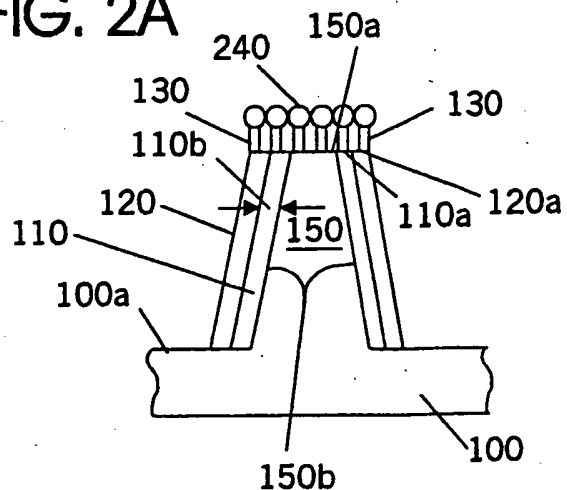


FIG. 2B

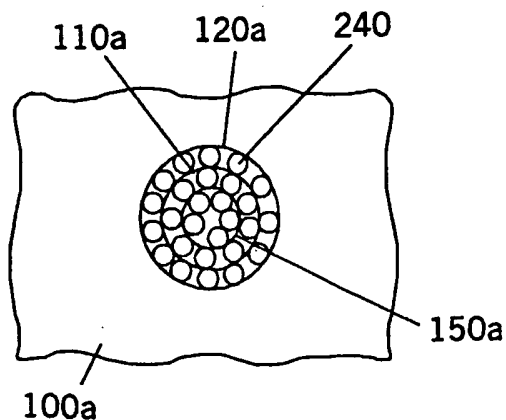


FIG. 2C

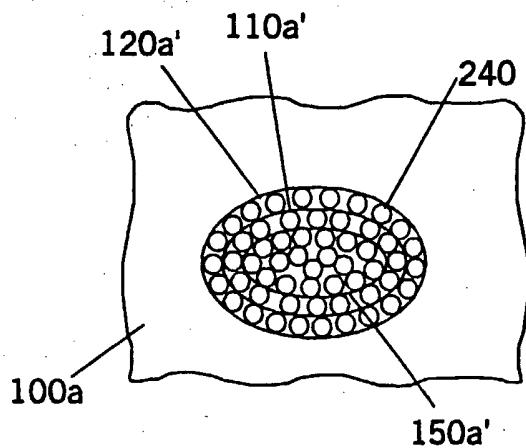


FIG. 2d

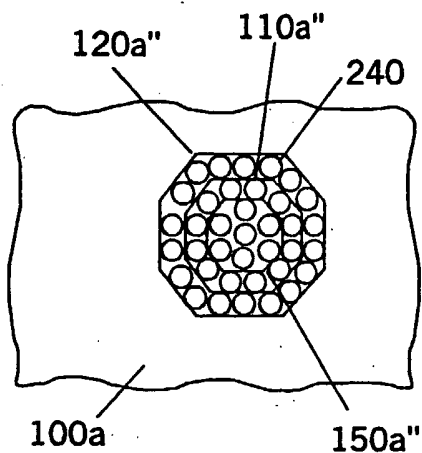


FIG. 3

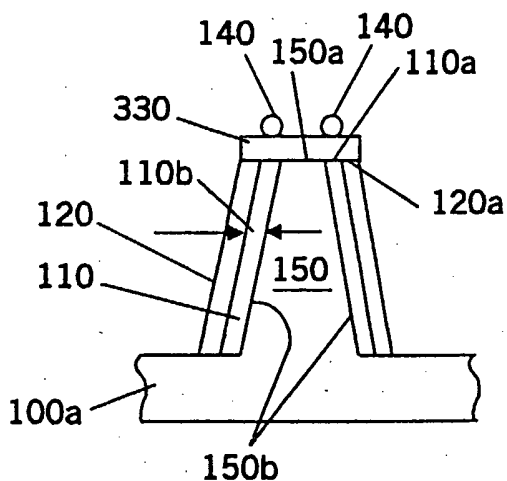


FIG. 4

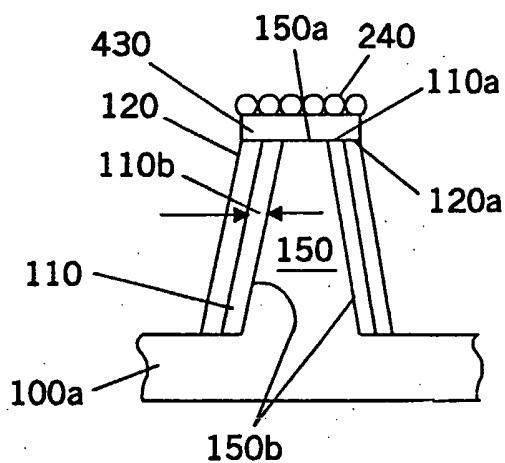


FIG. 5

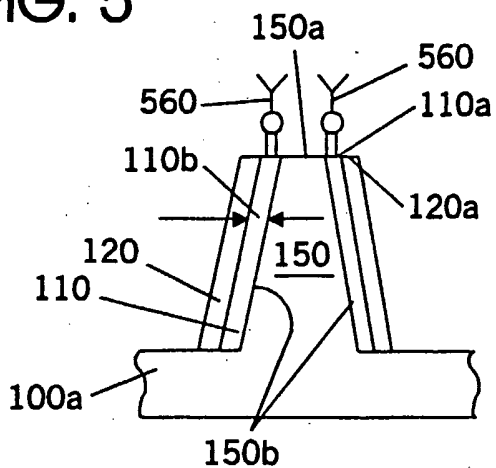
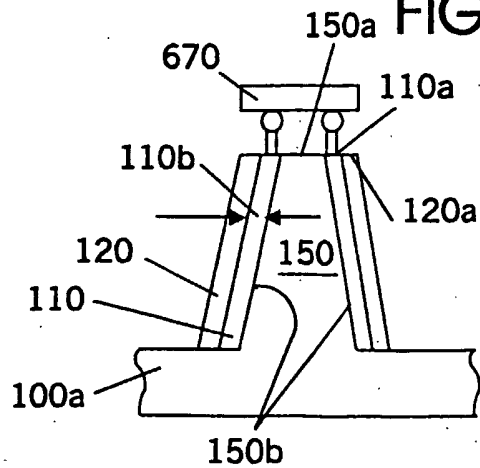


FIG. 6



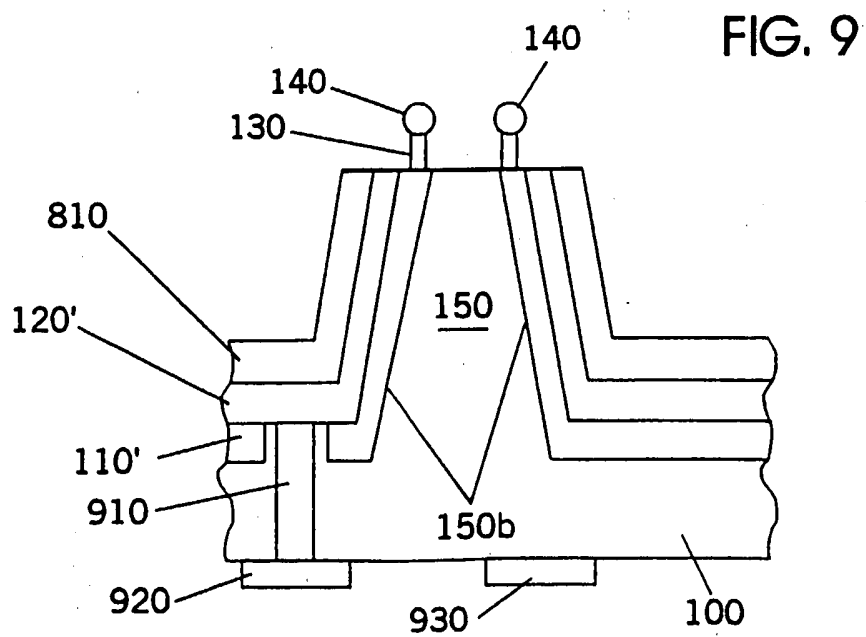
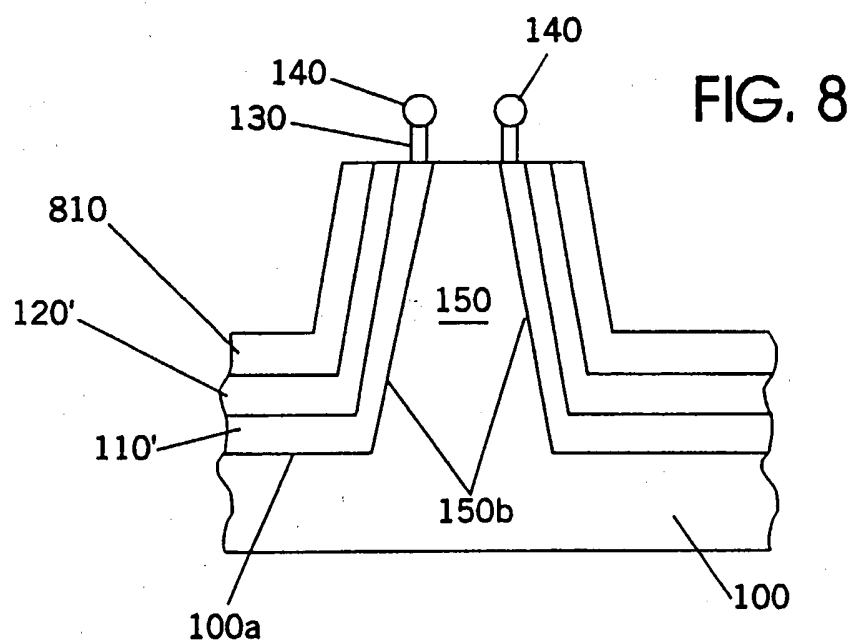


FIG. 10A

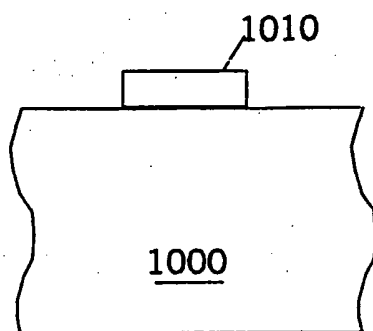


FIG. 10D

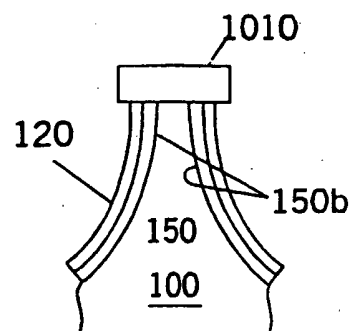


FIG. 10B

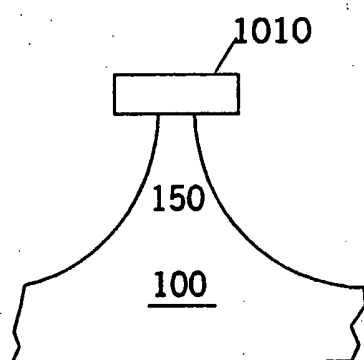


FIG. 10E

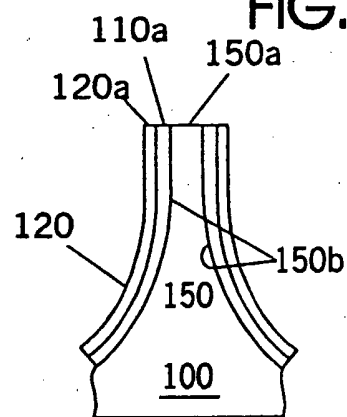


FIG. 10C

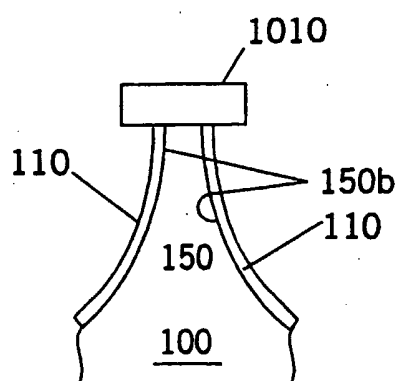


FIG. 10F

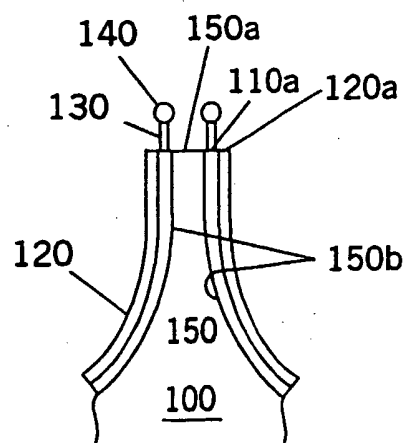


FIG. 11A

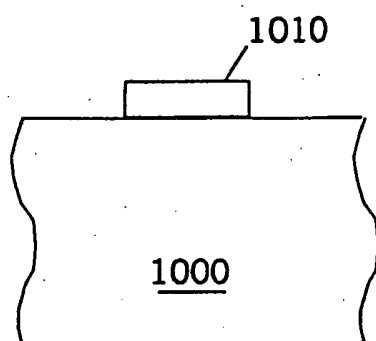


FIG. 11B

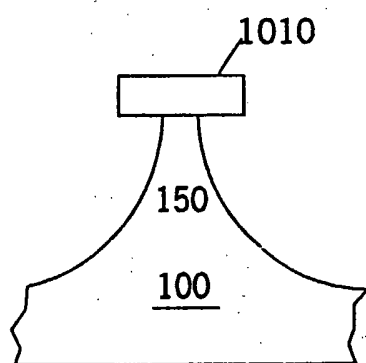


FIG. 11C

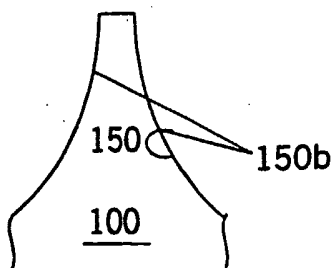


FIG. 11D

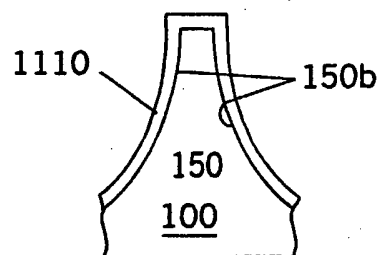


FIG. 11E

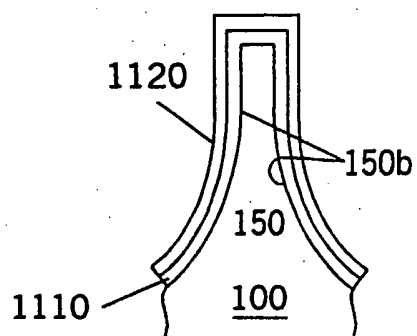


FIG. 11F

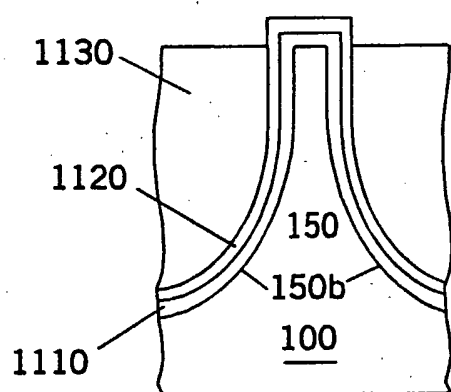


FIG. 11G

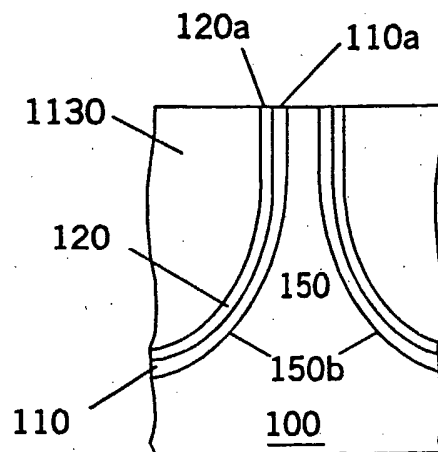


FIG. 11H

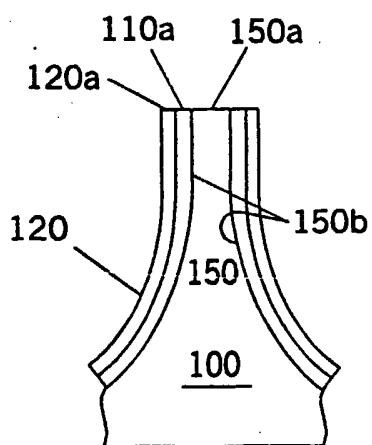


FIG. 11I

